

ABSTRACT OF THE DISCLOSURE

A method for fabricating a III-V Group compound semiconductor comprising a step of epitaxially growing on an $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer of lower Al content an $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer of higher Al content, in which step a growth rate of the $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer of higher Al content is made slower than a growth rate of the $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer of lower Al content, thereby effectively inhibiting the occurrence of starting points of abnormal growth at the interface between the two layers.